



STL180N4LLF6

N-channel 40 V, 1.8 mΩ, 34 A, PowerFLAT™ 5x6
STripFET™ VI DeepGATE Power MOSFET

Preliminary data

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
STL180N4LLF6	40 V	2.1 mΩ	34 A ⁽¹⁾

1. The value is rated according to R_{thj-pcb}

- Low gate charge
- Very low on-resistance
- High avalanche ruggedness

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using STMicroelectronics' STripFET™V technology. The device has been optimized to achieve very low on-state resistance, contributing to an FOM that is among the best in its class.



Figure 1. Internal schematic diagram

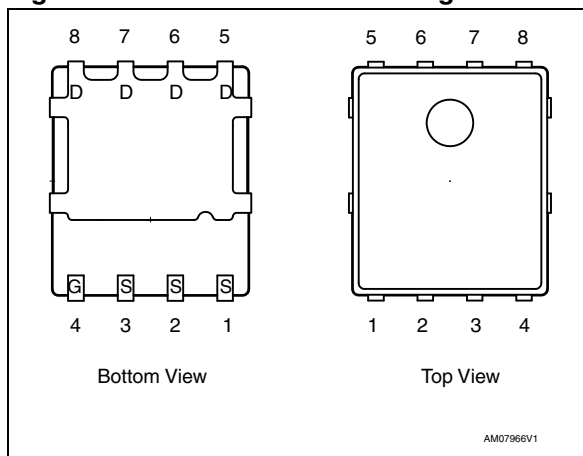


Table 1. Device summary

Order code	Marking	Package	Packaging
STL180N4LLF6	180N4LLF6	PowerFLAT™ 5x6	Tape and reel

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
3	Test circuits	6
4	Package mechanical data	7
5	Revision history	11

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	40	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	180	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	115	A
$I_D^{(1)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^{\circ}\text{C}$	34	A
$I_D^{(1)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^{\circ}\text{C}$	21	A
$I_{DM}^{(2)}$	Drain current (pulsed)	720	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	136	W
$P_{TOT}^{(1)}$	Total dissipation at $T_{pcb} = 25\text{ }^{\circ}\text{C}$	5	W
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 175	$^{\circ}\text{C}$

1. When mounted on FR-4 board of 1inch², 2oz Cu, $t < 10\text{ sec}$
2. Pulse width limited by safe operating area

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.1	$^{\circ}\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.3	$^{\circ}\text{C/W}$

1. When mounted on FR-4 board of 1inch², 2oz Cu, $t < 10\text{ sec}$

2 Electrical characteristics

($T_{CASE}=25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS}=0$)	$I_D = 250\text{ }\mu\text{A}$	40			V
I_{DSS}	Zero gate voltage drain current ($V_{GS}=0$)	$V_{DS} = 40\text{ V}$ $V_{DS} = 40\text{ V } T_C=125\text{ }^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS}=0$)	$V_{GS} = \pm 20\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS}=V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS}=10\text{ V}$, $I_D=17\text{ A}$ $V_{GS}=4.5\text{ V}$, $I_D=17\text{ A}$		1.8	2.1 3.4	$\text{m}\Omega$ $\text{m}\Omega$

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS}=25\text{ V}$, $f=1\text{ MHz}$, $V_{GS}=0$	-	6750	-	pF
C_{oss}	Output capacitance			1100		pF
C_{rss}	Reverse transfer capacitance			600		pF
Q_g	Total gate charge	$V_{DD}=15\text{ V}$, $I_D = 34\text{ A}$ $V_{GS}=4.5\text{ V}$ <i>Figure 3</i>	-	63	-	nC
Q_{gs}	Gate-source charge			TBD		
Q_{gd}	Gate-drain charge			TBD		

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=37\text{ V}$, $I_D=10\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ <i>Figure 2</i>	-	TBD	-	ns
t_r	Rise time			TBD		ns
$t_{d(off)}$	Turn-off delay time			TBD		ns
t_f	Fall time			TBD		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current		-		19	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		80	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=19\text{ A}$, $V_{GS}=0$	-		1.3	V
t_{rr}	Reverse recovery time	$I_{SD}=19\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$, $V_{DD}=120\text{ V}$, $T_i=150\text{ }^\circ\text{C}$	-	TBD		ns
Q_{rr}	Reverse recovery charge			TBD		nC
I_{RRM}	Reverse recovery current			TBD		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

3 Test circuits

Figure 2. Switching times test circuit for resistive load

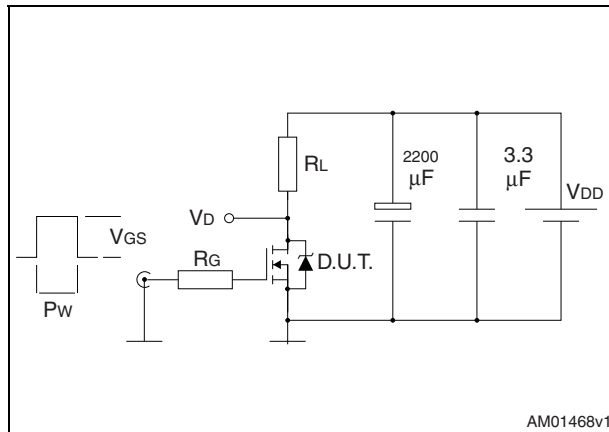


Figure 3. Gate charge test circuit

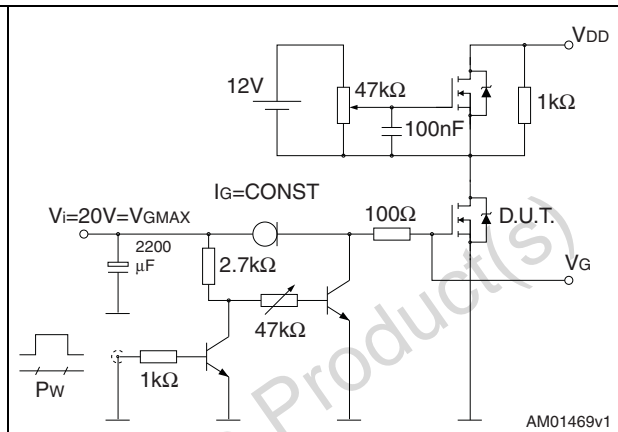


Figure 4. Test circuit for inductive load switching and diode recovery times

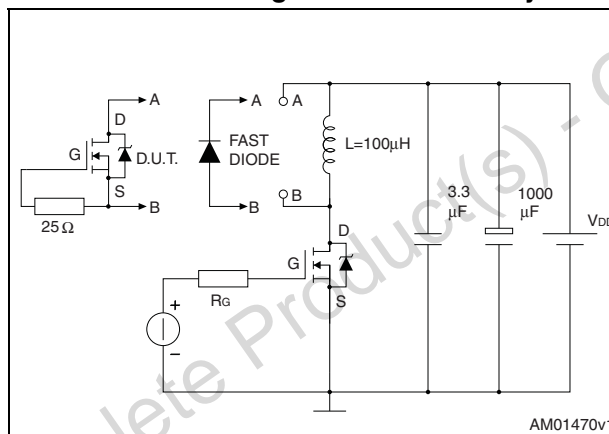


Figure 5. Unclamped inductive load test circuit

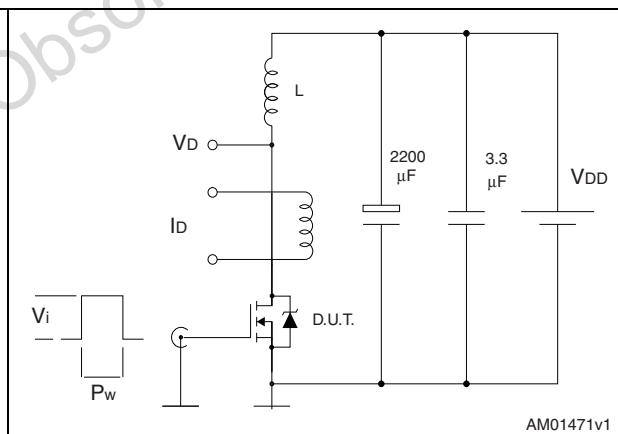


Figure 6. Unclamped inductive waveform

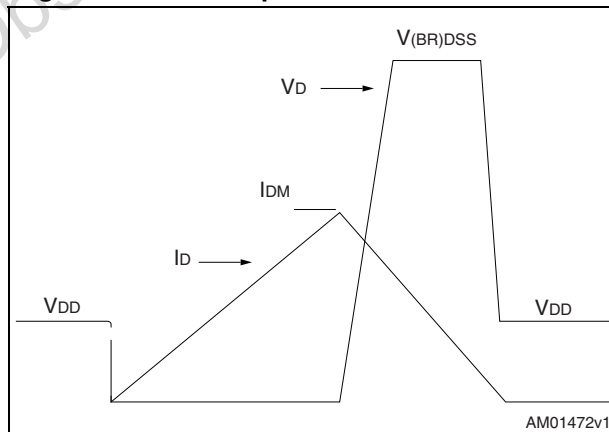
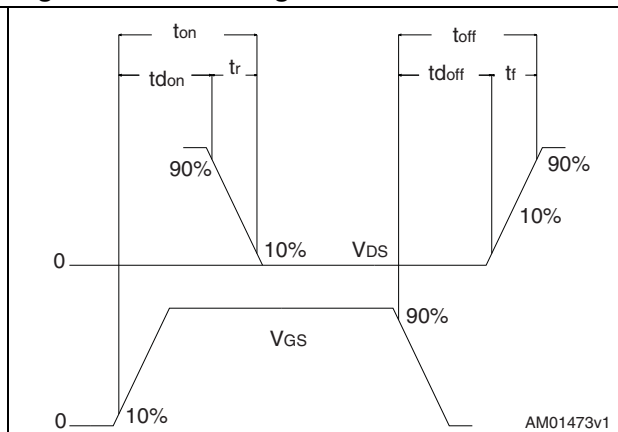


Figure 7. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Obsolete Product(s) - Obsolete Product(s)

Table 8. PowerFLAT™ 5x6 type S-C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D		5.20	
E		6.15	
D2	4.11		4.31
E2	3.50		3.70
e		1.27	
e1		0.65	
L	0.715		1.015
K	1.05		1.35

Figure 8. PowerFLAT™ 5x6 type S-C drawing

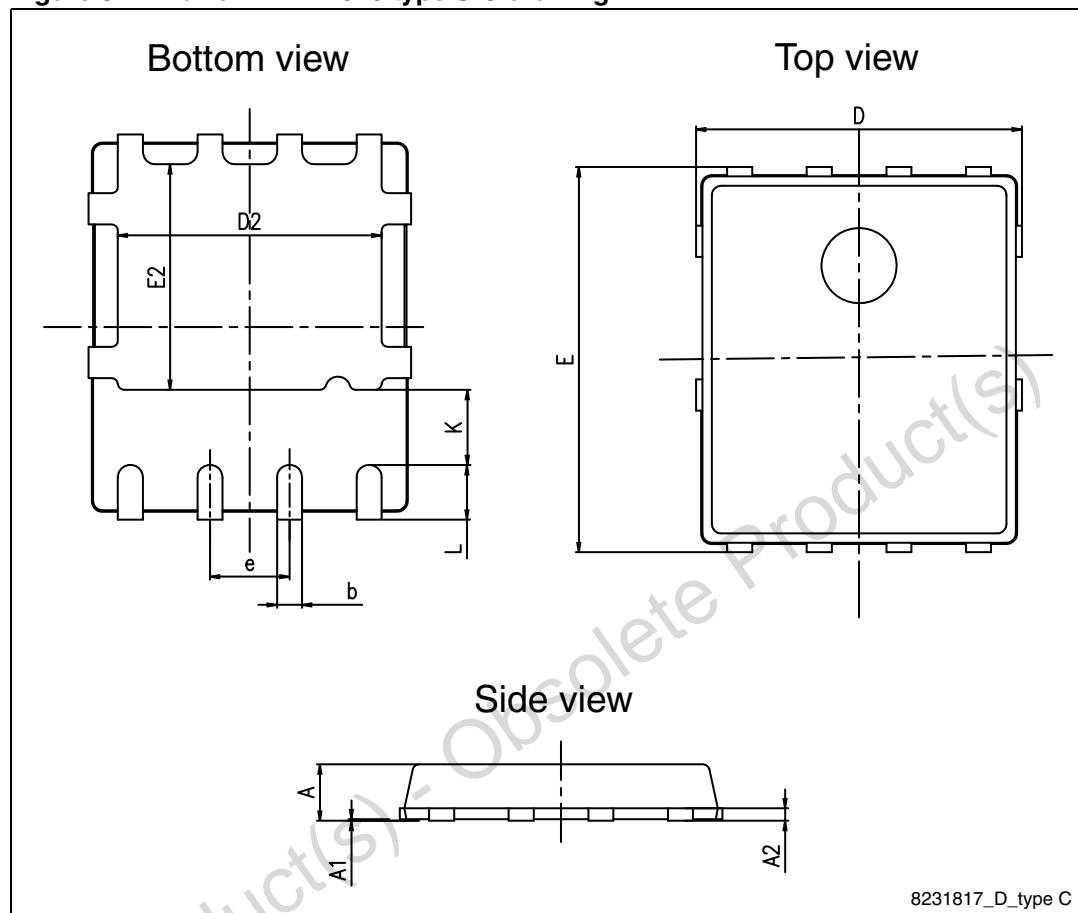
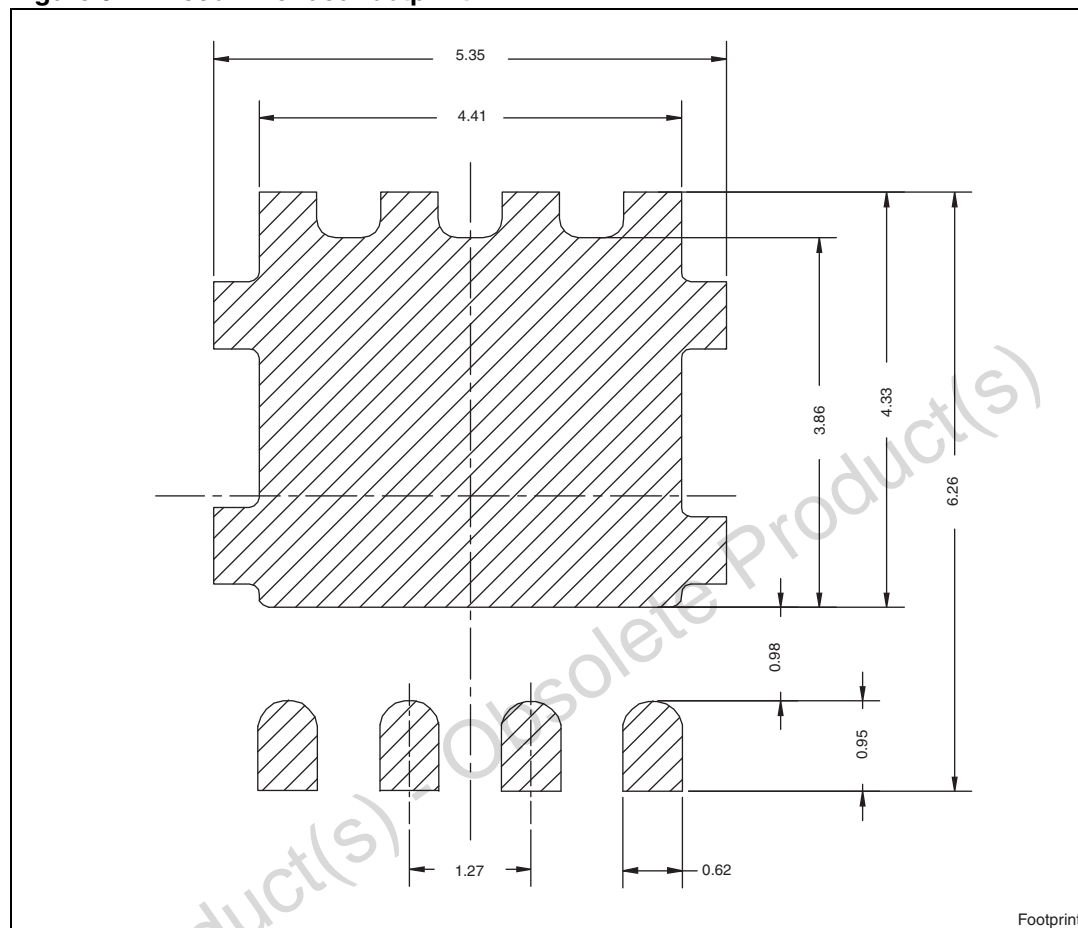


Figure 9. Recommended footprint

5 Revision history

Table 9. Document revision history

Date	Revision	Changes
27-Sep-2011	1	First release.
22-Nov-2011	2	Updated test conditions for Gate charge in Table 5: Dynamic .

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY TWO AUTHORIZED ST REPRESENTATIVES, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2011 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com